

# Corrections to “Design, Optimization, and Realization of a High Performance MOEMS Accelerometer From a Double-Device-Layer SOI Wafer”

Qianbo Lu<sup>id</sup>, *Student Member, IEEE*, Jian Bai, Kaiwei Wang<sup>id</sup>, and Sailing He<sup>id</sup>, *Fellow, IEEE*

In the above article [1], the content of this article remains untouched. Only Table III is rectified. The stiffness of the proposed MOEMS accelerometer listed in Table III should be half of that value, which is 0.56 N/m.

Table III should be as follows:

TABLE III  
PERFORMANCE COMPARISON OF THE PROPOSED ACCELEROMETER TO THE TYPICAL HIGHLY SENSITIVE ACCELEROMETERS

Specification	Proposed MOEMS accelerometer	Closed-loop capacitance [11]	Photonic -crystal nanocavity [23]	In-plane capacitance [12]	Optomechanical [20]
Proof mass	8.7 mg	1.62 μg	0.14 μg	38 mg	1.2 mg
Stiffness	0.59 N/m	93.48 N/m	1.49 N/m	57.35 N/m	1.51 N/m
Acceleration-displacement sensitivity	158.20 μm/g	0.17 μm/g	0.92 nm/g	6.50 μm/g	7.79 μm/g
Acceleration sensitivity	2486 V/g	950 mV/g	500 V/g	105 V/g	N/A
Frequency	35 Hz	500 Hz	20 kHz	200 Hz	220 Hz
Noise floor	185.8 ng/(Hz) <sup>0.5</sup>	1200 ng/(Hz) <sup>0.5</sup>	10 <sup>4</sup> ng/(Hz) <sup>0.5</sup>	213 ng/(Hz) <sup>0.5</sup>	43.7 ng/(Hz) <sup>0.5</sup> (thermal noise floor)

## REFERENCES

- [1] Q. Lu *et al.*, “Design, optimization, and realization of a high-performance MOEMS accelerometer from a double-device-layer SOI wafer,” *J. Microelectromech. Syst.*, vol. 26, no. 4, pp. 859–869, Aug. 2017.

Manuscript received December 22, 2020; accepted December 27, 2020. Date of current version March 16, 2021. (*Corresponding author: Qianbo Lu.*)

The authors are with the College of Optical Science and Engineering, Zhejiang University, Hangzhou 310027, China (e-mail: luqianbo@126.com; bai@zju.edu.cn; wangkaiwei@zju.edu.cn; sailing@zju.edu.cn).

Color versions of one or more figures in this article are available at <https://doi.org/10.1109/JMEMS.2020.3048739>.

Digital Object Identifier 10.1109/JMEMS.2020.3048739